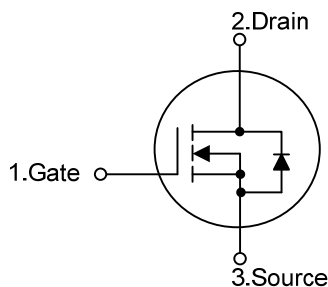


**11NM60-U2****Power MOSFET****11A, 600V N-CHANNEL
SUPER-JUNCTION MOSFET****DESCRIPTION**

The **UTC 11NM60-U2** is a Super Junction MOSFET Structure and is designed to have better characteristics, such as fast switching time, low gate charge, low on-state resistance and a high rugged avalanche characteristics. This power MOSFET is usually used at DC-DC, AC-DC converters for power applications.

FEATURES

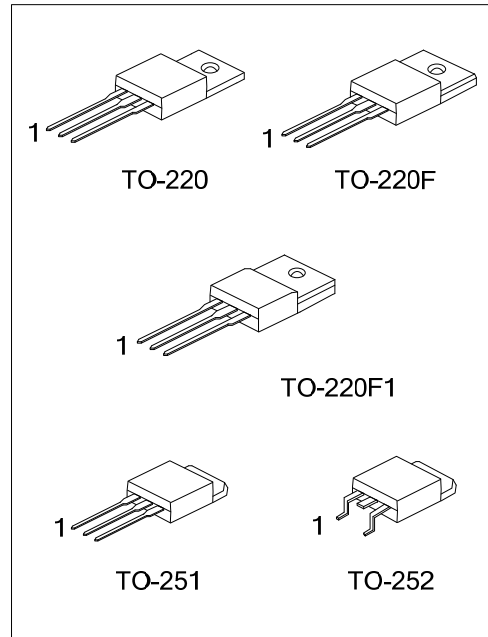
- * $R_{DS(ON)} < 0.5\Omega$ @ $V_{GS}=10V$, $I_D=5.5A$
- * By using Super Junction Structure
- * Fast Switching
- * With 100% Avalanche Tested

SYMBOL**ORDERING INFORMATION**

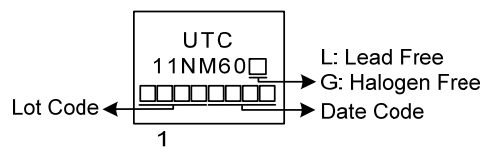
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
11NM60L-TA3-T	11NM60G-TA3-T	TO-220	G	D	S	Tube
11NM60L-TF3-T	11NM60G-TF3-T	TO-220F	G	D	S	Tube
11NM60L-TF1-T	11NM60G-TF1-T	TO-220F1	G	D	S	Tube
11NM60L-TM3-T	11NM60G-TM3-T	TO-251	G	D	S	Tube
11NM60L-TN3-R	11NM60G-TN3-R	TO-252	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

11NM60G-TA3-T (1)Packing Type (2)Package Type (3)Green Package		(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF3: TO-220F, TF1: TO-220F1, TM3: TO-251, TN3: TO-252 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_c = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	11	A
	Pulsed (Note 2)	I_{DM}	33	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	425	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	18	V/ns
Power Dissipation	TO-220	P_D	80	W
	TO-220F/TO-220F1		30	W
	TO-251/TO-252		60	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature Range		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L=132\text{mH}$, $I_{AS}=2.54\text{A}$, $V_{DD}=50\text{V}$, $R_G=25\Omega$, Starting $T_J=25^\circ\text{C}$

4. $I_{SD}\leq 11\text{A}$, $di/dt\leq 200\text{A}/\mu\text{s}$, $V_{DD}\leq BV_{DSS}$, Starting $T_J=25^\circ\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/TO-220F	θ_{JA}	62.5	$^\circ\text{C/W}$
	TO-220F1			
	TO-251/TO-252		110	
Junction to Case	TO-220	θ_{JC}	1.56	$^\circ\text{C/W}$
	TO-220F/TO-220F1		4.16	
	TO-251/TO-252		2.08	

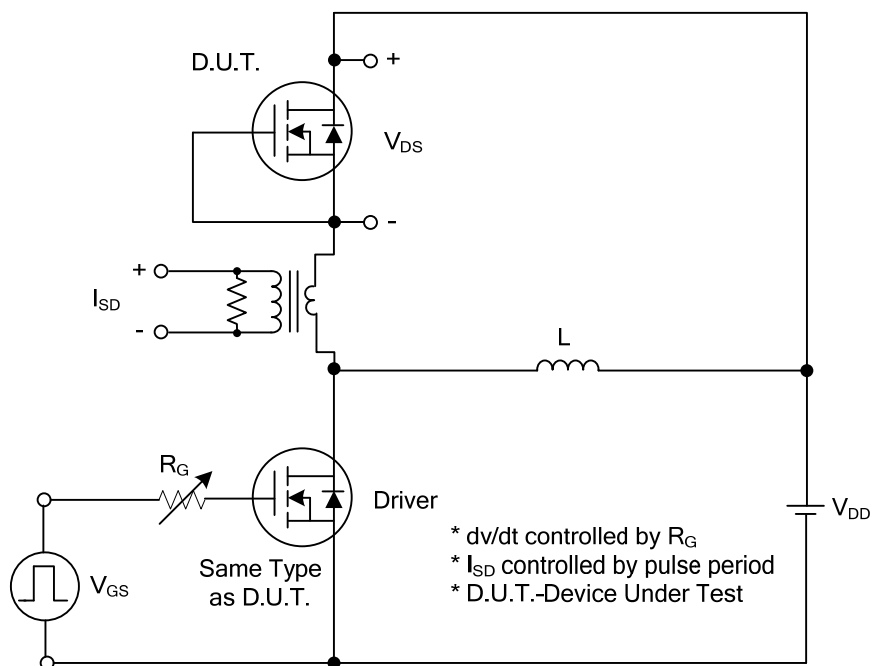
■ **ELECTRICAL CHARACTERISTICS** ($T_J=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} =0V, I _D =250μA	600			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =600V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{DS} =0V ,V _{GS} =30V			100	nA
	Reverse		V _{DS} =0V ,V _{GS} =-30V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D =250μA	2.5		4.5	V
Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =5.5A			0.5	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		670		pF
Output Capacitance		C _{OSS}			520		pF
Reverse Transfer Capacitance		C _{RSS}			50		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =100V, V _{GS} =10V, I _D =11A , I _G =1mA (Note 1, 2)		26		nC
Gate to Source Charge		Q _{GS}			8		nC
Gate to Drain Charge		Q _{GD}			10		nC
Turn-ON Delay Time (Note 1)		t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =11A, R _G =25Ω (Note 1, 2)		11.2		ns
Rise Time		t _R			24		ns
Turn-OFF Delay Time		t _{D(OFF)}			72		ns
Fall-Time		t _F			45		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				11	A
Maximum Body-Diode Pulsed Current		I _{SM}				33	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =11A, V _{GS} =0V			1.4	V
Body Diode Reverse Recovery Time (Note 1)		t _{rr}	I _S =11A, V _{GS} =0V,		430		ns
Body Diode Reverse Recovery Charge		Q _{rr}	dl _F /dt=100A/μs		3.8		μC

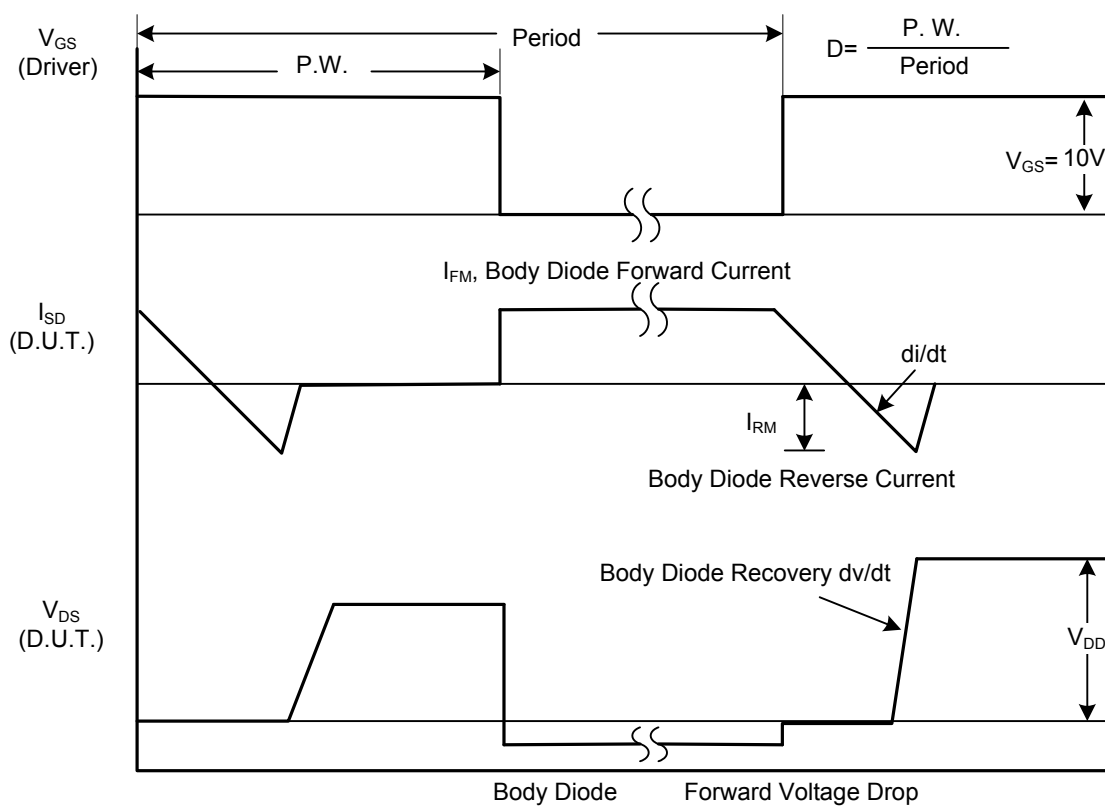
Notes: 1. Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

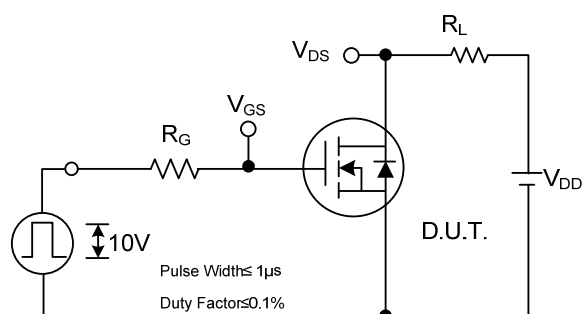


Peak Diode Recovery dv/dt Test Circuit

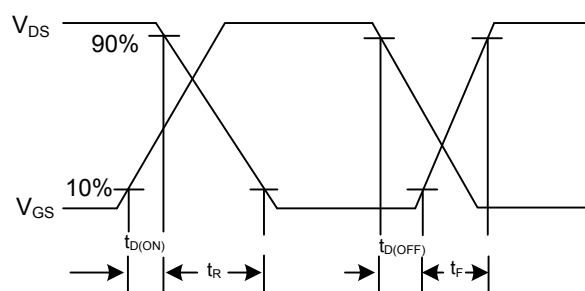


Peak Diode Recovery dv/dt Waveforms

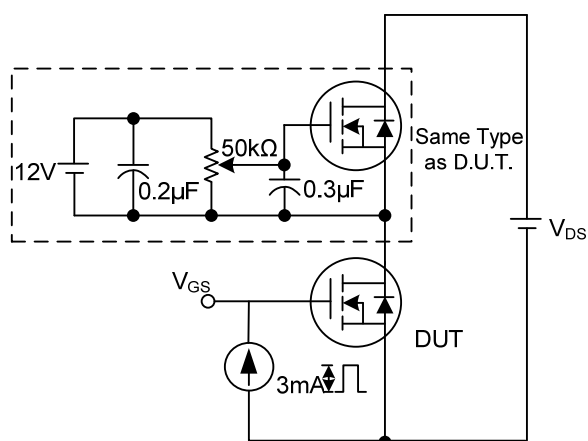
■ TEST CIRCUITS AND WAVEFORMS (Cont.)



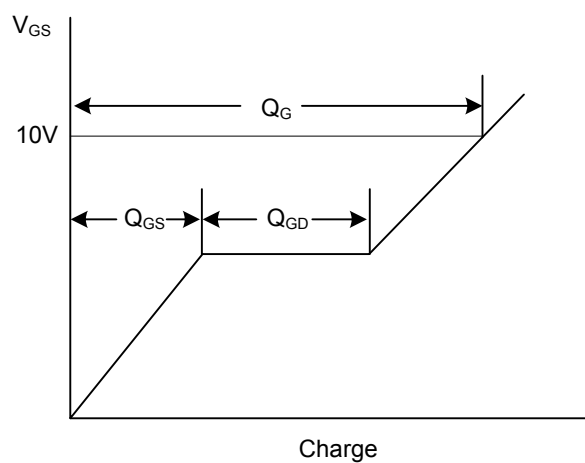
Switching Test Circuit



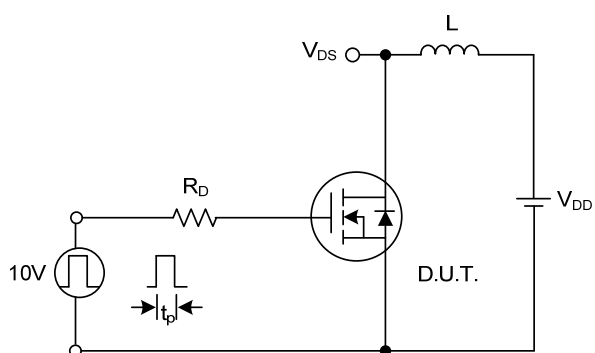
Switching Waveforms



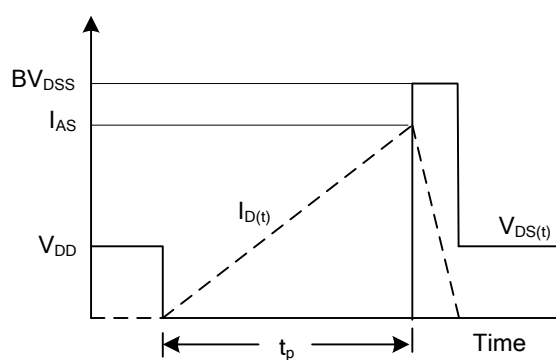
Gate Charge Test Circuit



Gate Charge Waveform

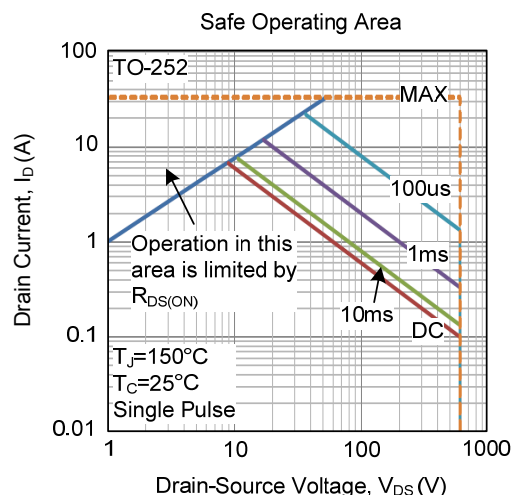
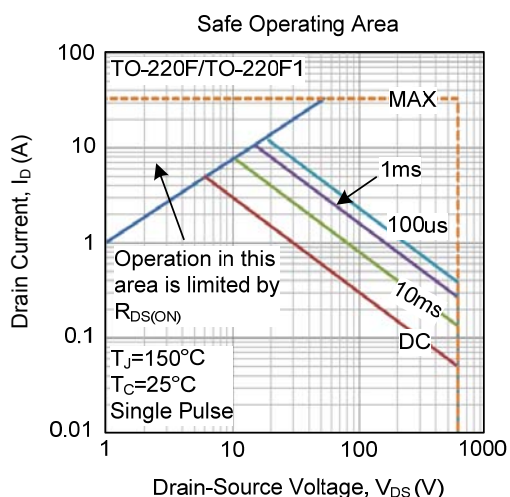
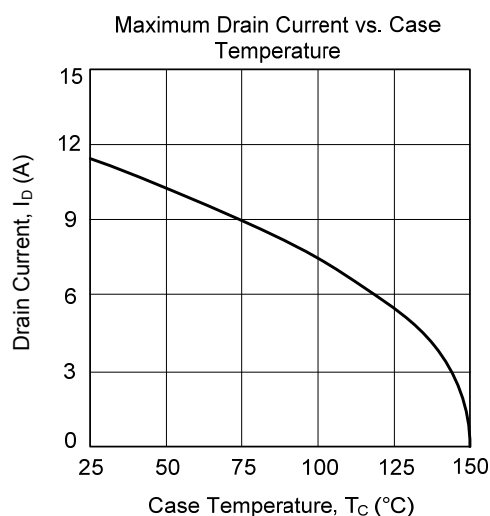
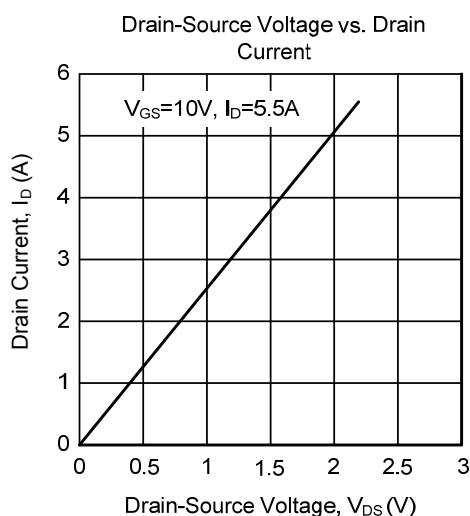


Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS



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